

- ✎ S296: (29) S291 and S295
- ✎ S297: (1210762) matrix array
- ✎ S298: (41984) S288 near S287
- ✎ S298: (4642) S284 near S297
- ✎ S300: (2510) S298 same S289
- ✎ S301: (0) S291 and S300
- ✎ S302: (82) S285 and S300
- ✎ S303: (71684) 1st transistor
- ✎ S304: (16501) S298 with S303
- ✎ S305: (41) S302 and S304
- ✎ S306: (1) 10/705406
- ✎ S307: (41) "669382".pn. "6331944".pn.
- ✎ S309: (28) 10/930512
- ✎ S309: (6) "669382".pn. "6331944".pn. "654480T".pn.
- ✎ S310: (2) "2003079617"
- ✎ S311: (5048) cap\$4 adj (metal film)
- ✎ S312: (279920) nitride
- ✎ S313: (1182674) (dep\$4 impurit\$3 (ion near\$3 implant\$3) diffus\$4)
- ✎ S314: (50) S317 with S312 with S313
- ✎ S315: (727096) transistor
- ✎ S316: (29) S314 and S315
- ✎ S317: (2) "20040262649"
- ✎ S318: (1) S317 and S313
- ✎ S319: (2) "6028002".pn.
- ✎ S320: (2) "20040235247"

20040285247

	U	I	Inventor	Document	Issn	P	Title	Current	Current I	Retrieval	S	C	P	3	Image	Doc
1	<input type="checkbox"/>	<input type="checkbox"/>	Hsu, Sheng	US 200402	2004110	Asymmetric crystalline structure mem	430/25	257/445.0				<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
2	<input type="checkbox"/>	<input type="checkbox"/>	EVANS, D R	US 200402	2004110	Formation of asymmetric crystalline st						<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040